

TO-92

Pin Definition:

1. Gate
2. Drain
3. Source

TSM1N60S

600V N-Channel Power MOSFET

PRODUCT SUMMARY

V_{DS} (V)	R_{DS(on)}(Ω)	I_D (A)
600	11 @ V _{GS} = 10V	0.3

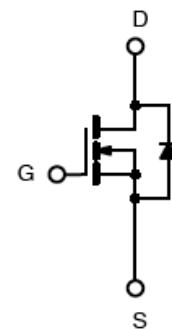
General Description

The TSM1N60S is used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. In addition, this advanced MOSFET is designed to withstand high energy in avalanche and commutation modes. The new energy efficient design also offers a drain- to-source diode with a fast recovery time. Designed for high voltage, high speed switching applications in power supplies, converters and PWM motor controls, these devices are particularly well suited for bridge circuits where diode speed and commutating safe operating areas are critical and offer additional and safety margin against unexpected voltage transients.

Features

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.
- I_{DSS} and V_{DS(on)} specified at elevated temperature

Block Diagram


N-Channel MOSFET

Ordering Information

Part No.	Package	Packing
TSM1N60SCT B0	TO-92	1Kpcs / Bulk
TSM1N60SCT A3	TO-92	2Kpcs / Ammo

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	600	V
Gate-Source Voltage	V _{GS}	±30	V
Continuous Drain Current	I _D	0.3	A
Pulsed Drain Current	I _{DM}	1.2	A
Continuous Source Current (Diode Conduction) ^{a,b}	I _S	1	A
Single Pulse Drain to Source Avalanche Energy (V _{DD} = 100V, V _{GS} =10V, I _{AS} =2A, L=10mH, R _G =25Ω)	EAS	50	mJ
Total Power Dissipation @T _C = 25°C	P _{DTOT}	3	W
Operating Junction Temperature	T _J	+150	°C
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C
Lead Temperature (1/8" from case)	T _L	10	S

Thermal Performance

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Ambient	$R\theta_{JA}$	125	°C/W
Thermal Resistance - Junction to Case	$R\theta_{JC}$	50	°C/W
Thermal Resistance - Junction to Lead	$R\theta_{JL}$	40	°C/W

Notes: Surface mounted on FR4 board $t \leq 10\text{sec}$

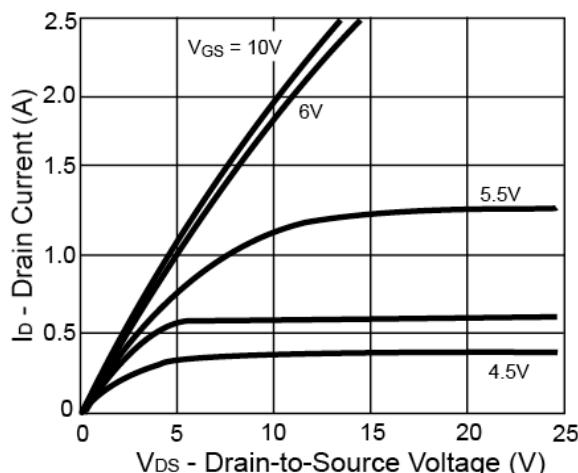
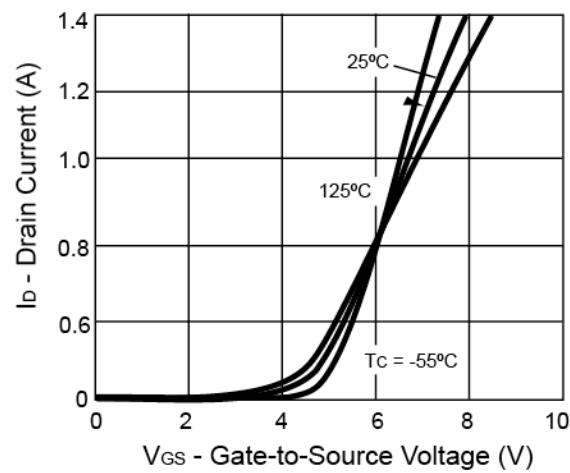
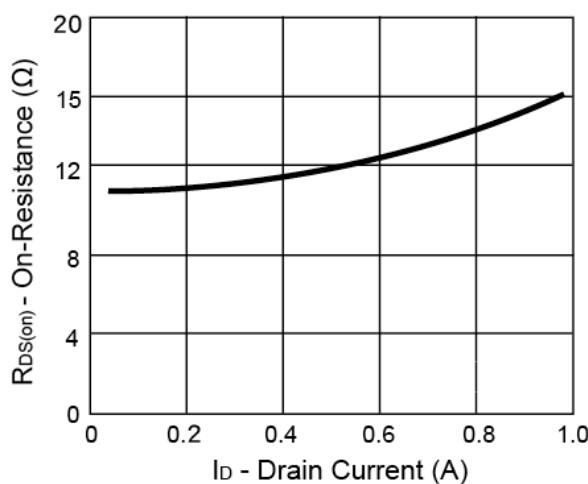
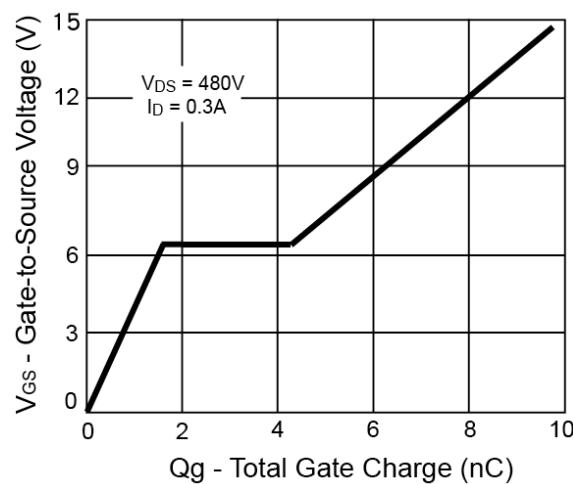
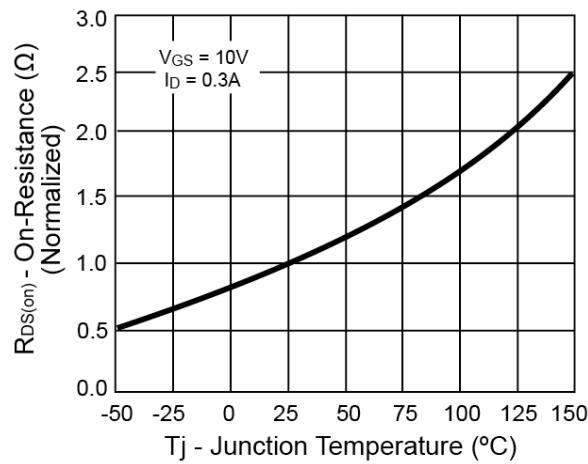
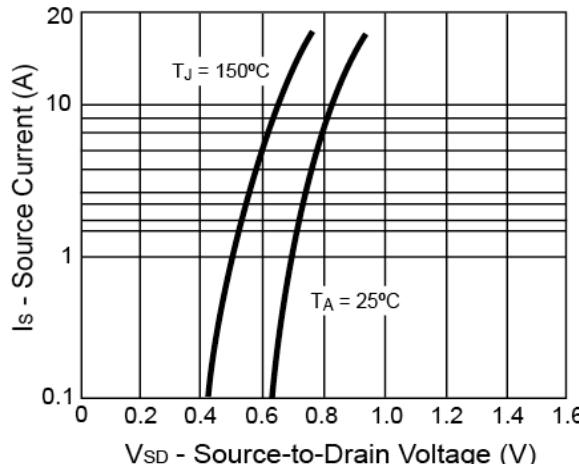
Electrical Specifications (Ta=25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$	BV_{DSS}	600	--	--	V
Drain-Source On-State Resistance	$V_{GS} = 10\text{V}, I_D = 0.3\text{A}$	$R_{DS(ON)}$	--	11	13	Ω
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	$V_{GS(TH)}$	2.0	--	4.0	V
Zero Gate Voltage Drain Current	$V_{DS} = 600\text{V}, V_{GS} = 0\text{V}$	I_{DSS}	--	--	10	uA
Gate Body Leakage	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$	I_{GSS}	--	--	± 100	nA
Forward Transconductance	$V_{DS} \geq 50\text{V}, I_D = 0.3\text{A}$	g_{fs}	--	5	--	S
Diode Forward Voltage	$I_S = 1\text{A}, V_{GS} = 0\text{V}$	V_{SD}	--	--	1.5	V
Dynamic^b						
Total Gate Charge	$V_{DS} = 400\text{V}, I_D = 1\text{A}, V_{GS} = 10\text{V}$	Q_g	--	4.5	6	nC
Gate-Source Charge		Q_{gs}	--	1.1	--	
Gate-Drain Charge		Q_{gd}	--	2	--	
Input Capacitance	$V_{DS} = 25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$	C_{iss}	--	155	200	pF
Output Capacitance		C_{oss}	--	20	26	
Reverse Transfer Capacitance		C_{rss}	--	3	4	
Switching^c						
Turn-On Delay Time	$V_{GS} = 10\text{V}, I_D = 1\text{A}, V_{DS} = 300\text{V}, R_G = 6\Omega$	$t_{d(on)}$	--	10	30	nS
Turn-On Rise Time		t_r	--	20	50	
Turn-Off Delay Time		$t_{d(off)}$	--	25	45	
Turn-Off Fall Time		t_f	--	24	60	

Notes:

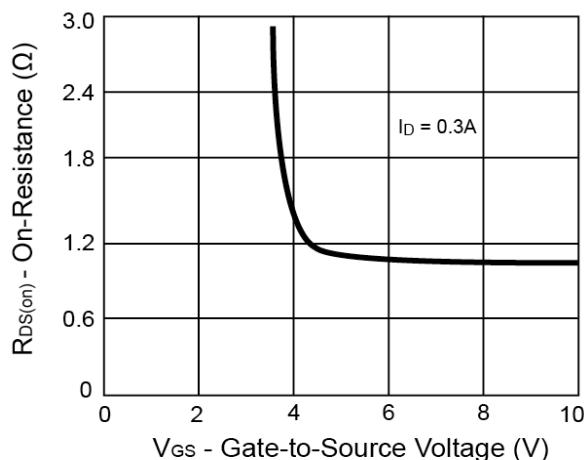
- Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$
- For design reference only, not subject to production testing.
- Switching time is essentially independent of operating temperature.

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

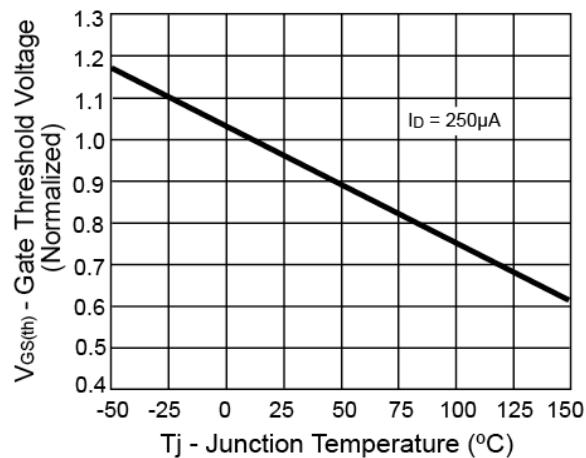
Output Characteristics

Transfer Characteristics

On-Resistance vs. Drain Current

Gate Charge

On-Resistance vs. Junction Temperature

Source-Drain Diode Forward Voltage


Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

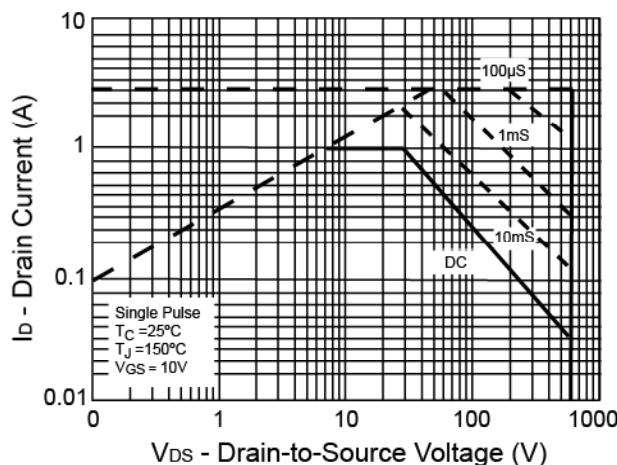
On-Resistance vs. Gate-Source Voltage



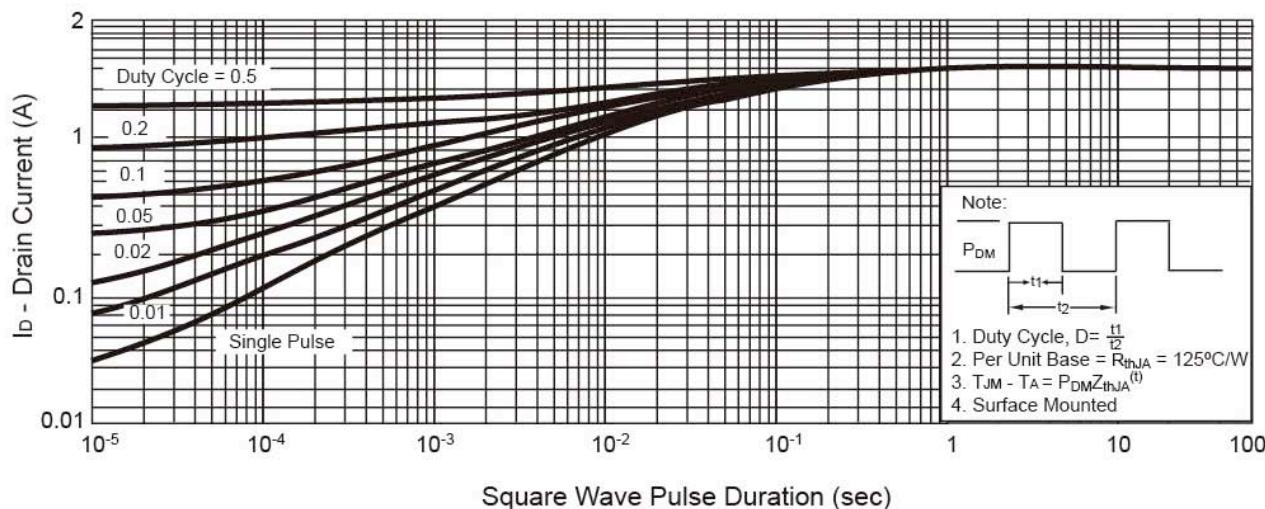
Threshold Voltage



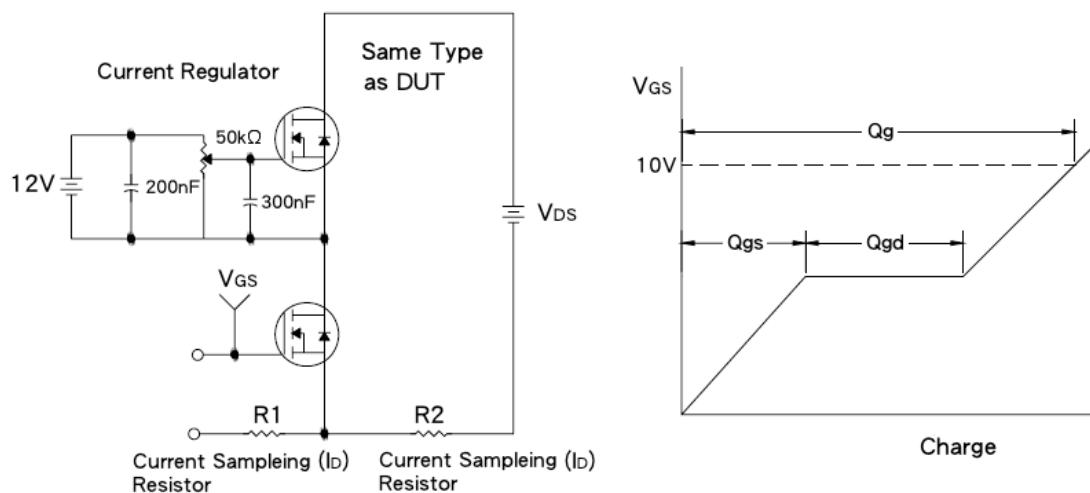
Maximum Safe Operating Area



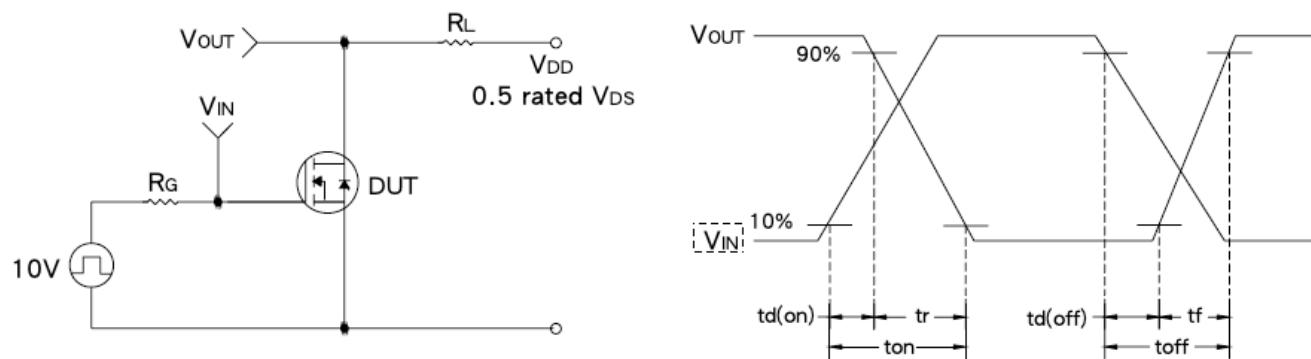
Normalized Thermal Transient Impedance, Junction-to-Ambient



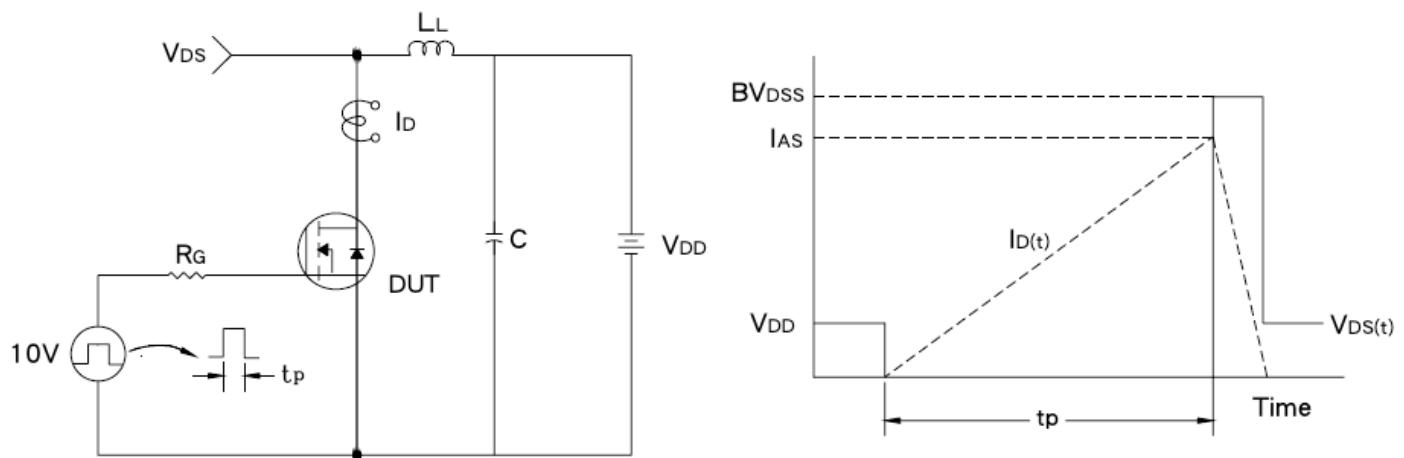
Gate Charge Test Circuit & Waveform



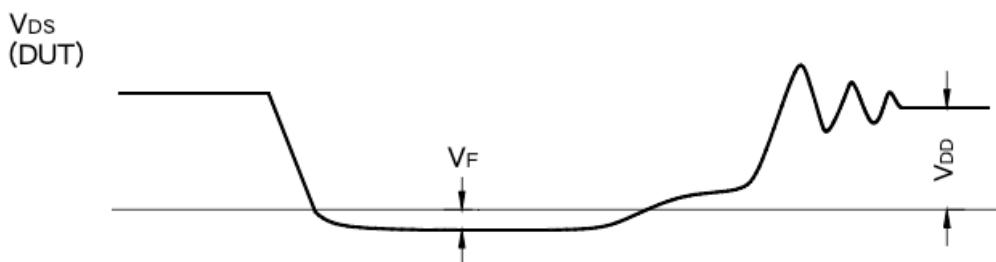
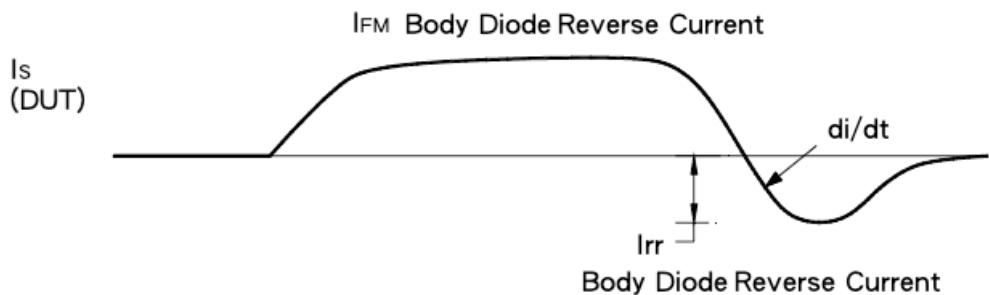
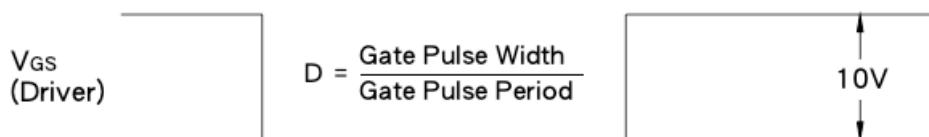
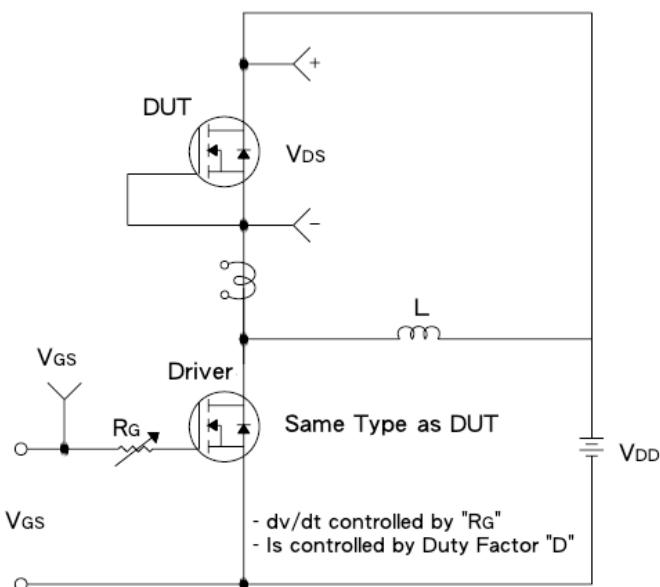
Resistive Switching Test Circuit & Waveform



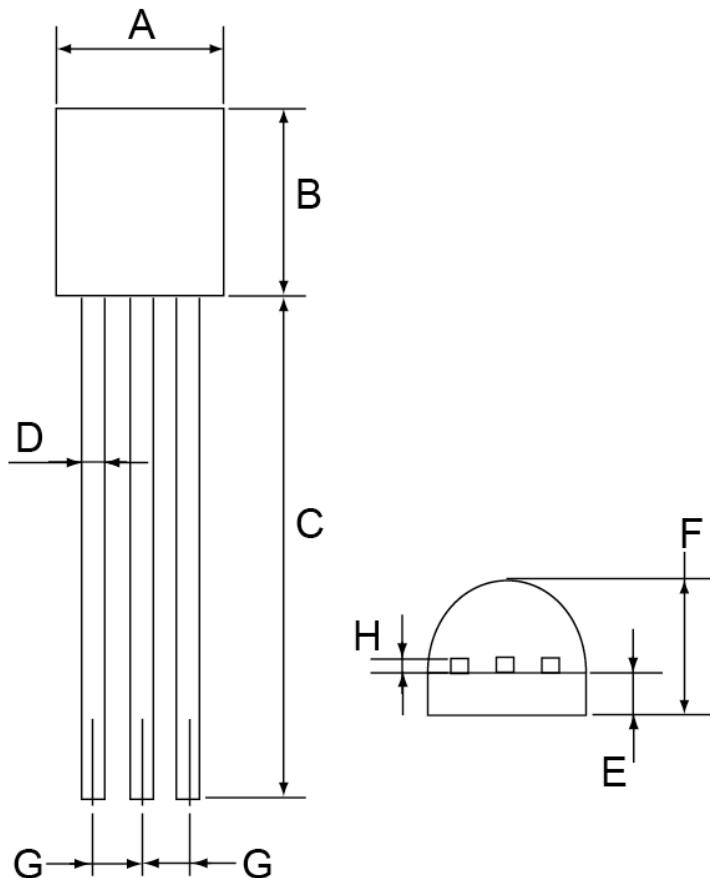
E_{AS} Test Circuit & Waveform



Diode Reverse Recovery Time Test Circuit & Waveform

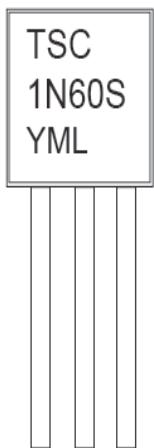


TO-92 Mechanical Drawing



TO-92 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.30	4.70	0.169	0.185
B	4.30	4.70	0.169	0.185
C	13.53 (typ)		0.532 (typ)	
D	0.39	0.49	0.015	0.019
E	1.18	1.28	0.046	0.050
F	3.30	3.70	0.130	0.146
G	1.27	1.31	0.050	0.051
H	0.33	0.43	0.013	0.017

Marking Diagram



Y = Year Code
M = Month Code
 (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep,
 J=Oct, K=Nov, L=Dec)
L = Lot Code

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